FIG. 1A

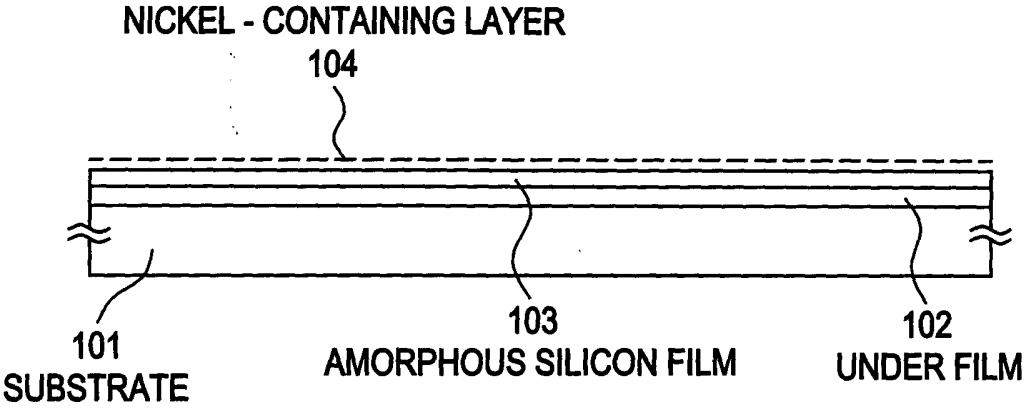


FIG. 1B

LASER CRYSTALLIZATION STEP

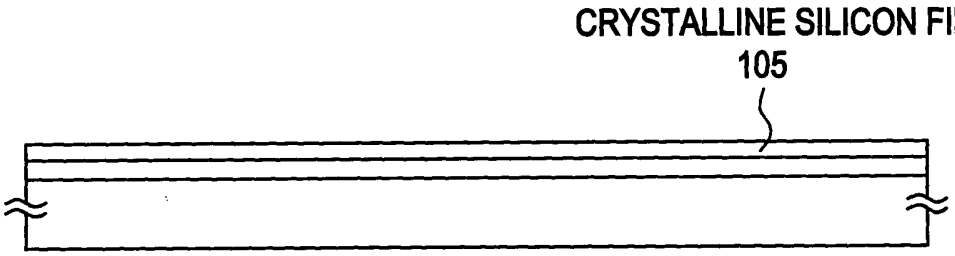


FIG. 1C

THERMAL TREATMENT STEP IN REDUCING ATMOSPHERE

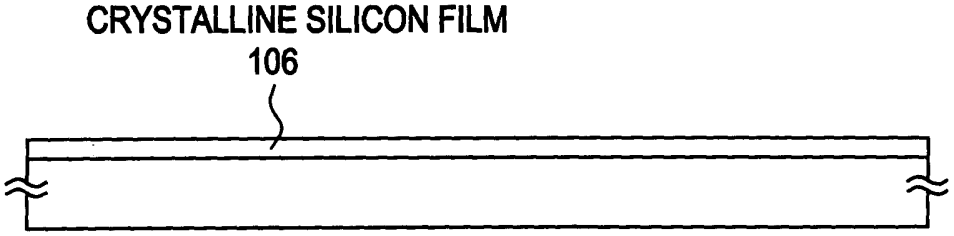


FIG. 2A

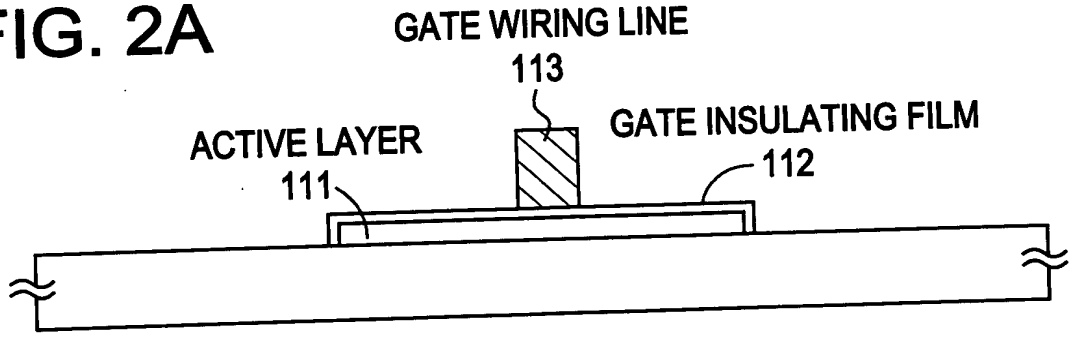


FIG. 2B

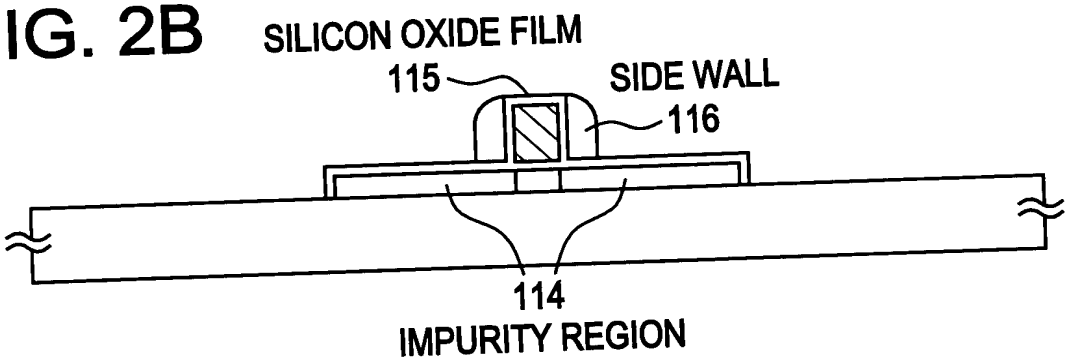


FIG. 2C

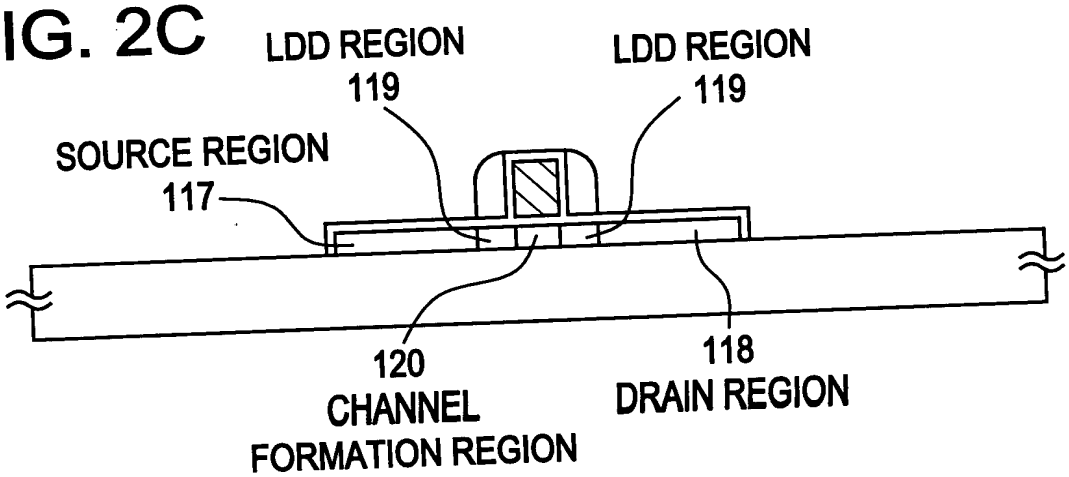


FIG. 2D

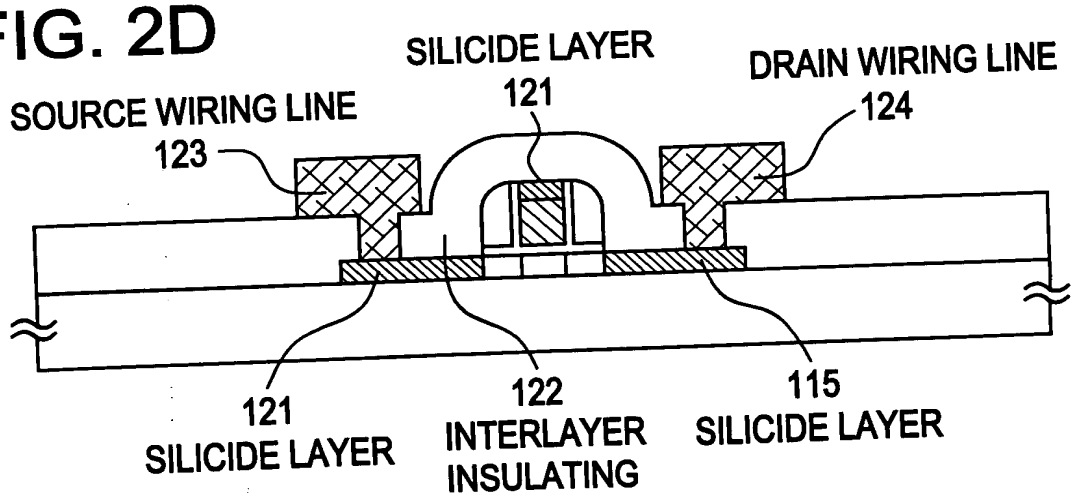


FIG. 3A

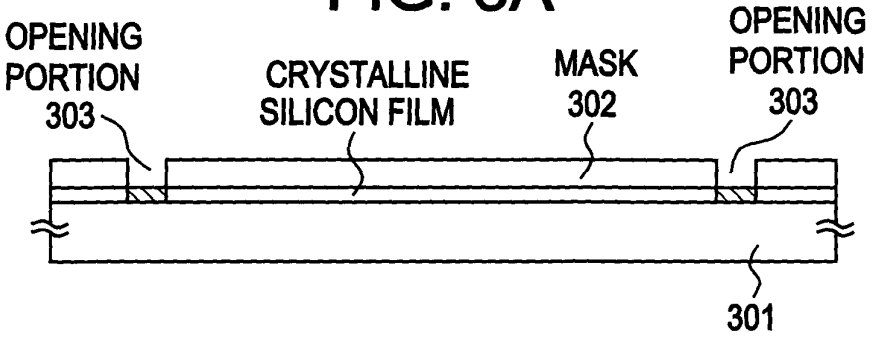
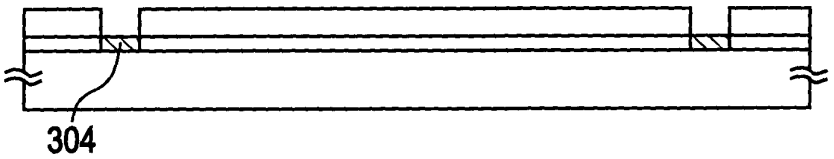


FIG. 3B

ADDING STEP OF PHOSPHORUS



GETTERING REGION

FIG. 3C

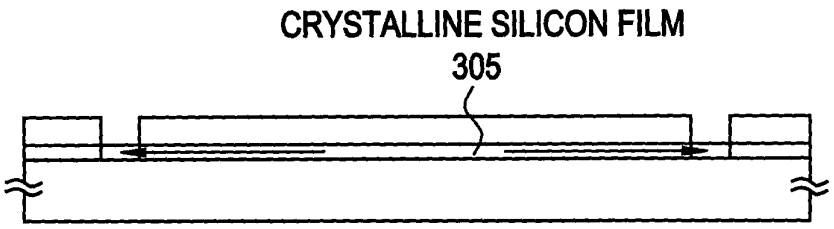


FIG. 3D

HEAT TREATMENT STEP IN REDUCING ATMOSPHERE

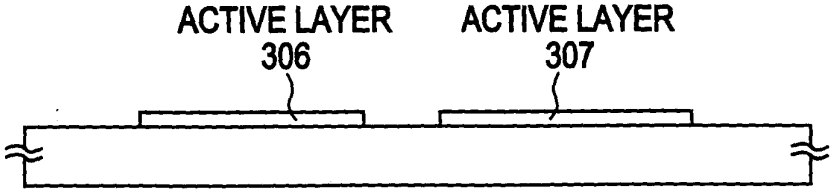


FIG. 4A

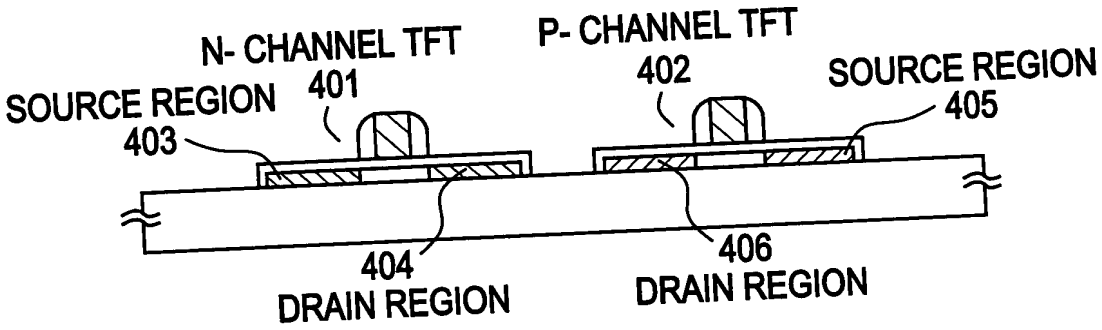


FIG. 4B

GETTERING STEP

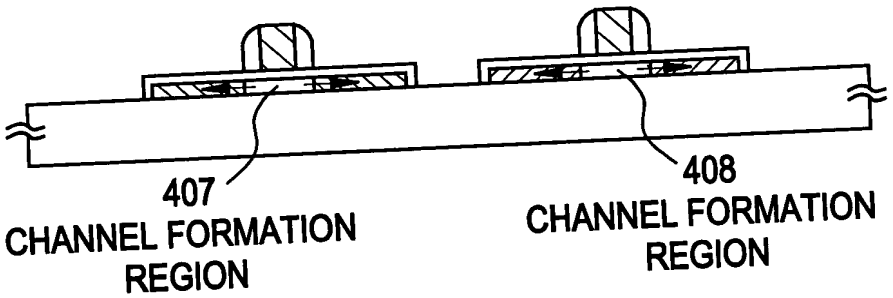
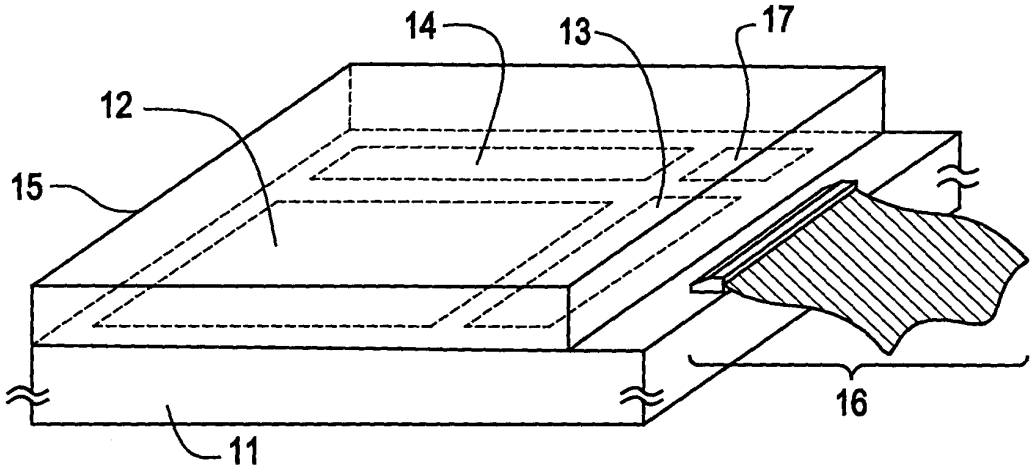


FIG. 5A



11: SUBSTRATE HAVING INSULATING SURFACE
12: PIXEL MATRIX CIRCUIT
13: SOURCE DRIVER CIRCUIT
14: GATE DRIVER CIRCUIT
15: OPPOSITE SUBSTRATE
16: FPC
17: SIGNAL PROCESSING CIRCUIT

FIG. 5B

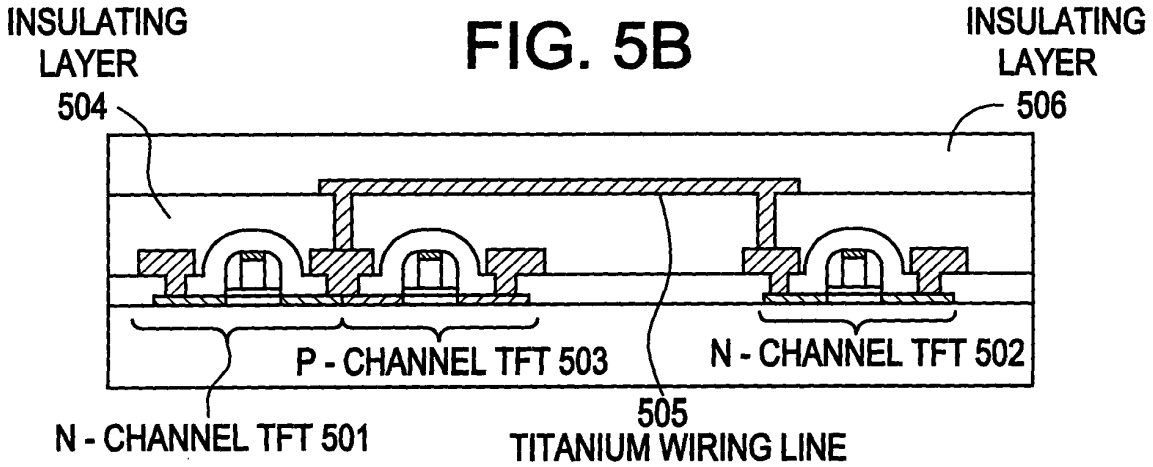


FIG. 5C

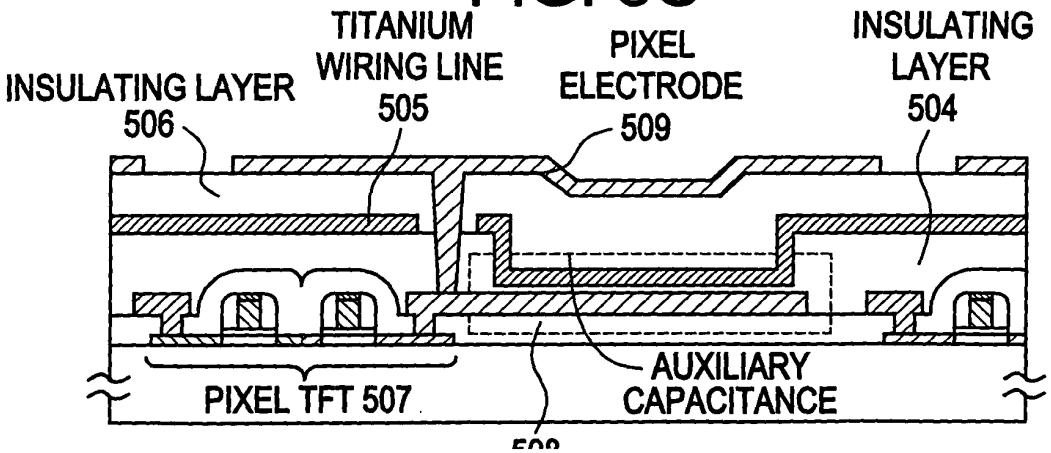


FIG. 6

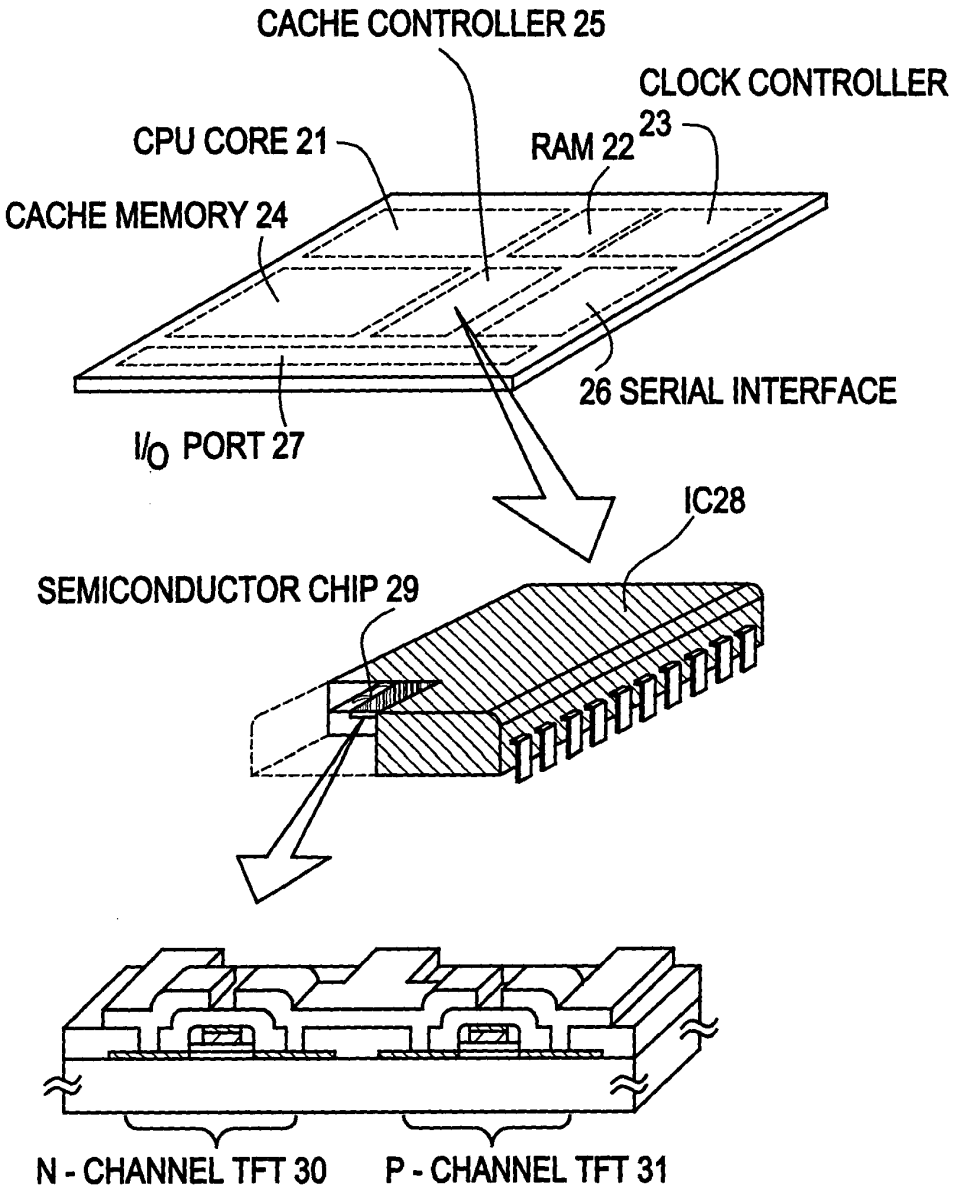


FIG. 7A

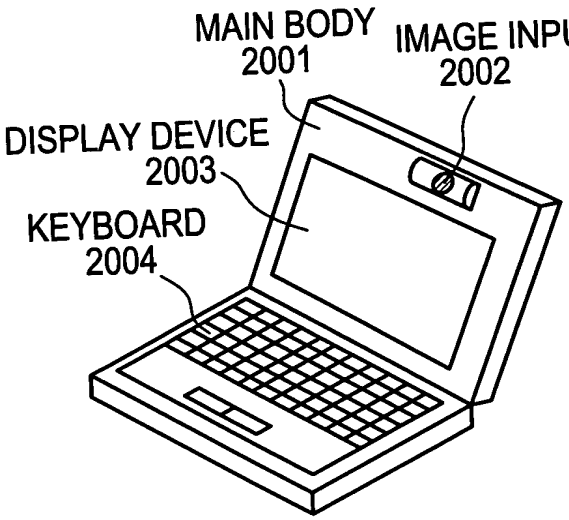


FIG. 7B

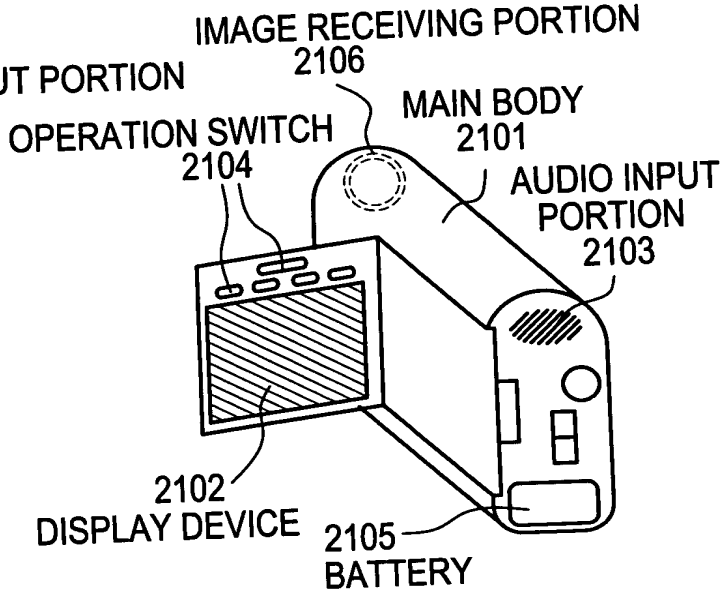


FIG. 7C

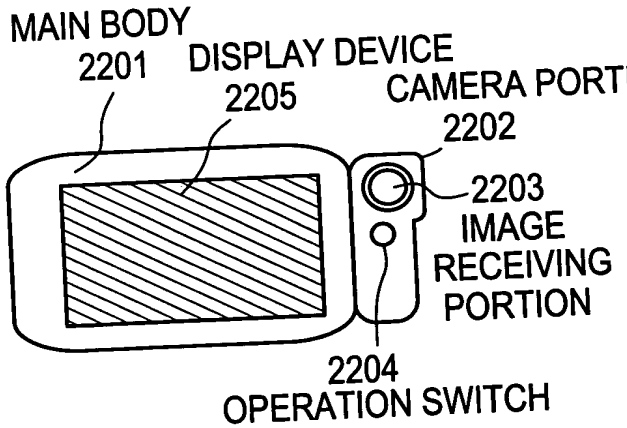


FIG. 7D

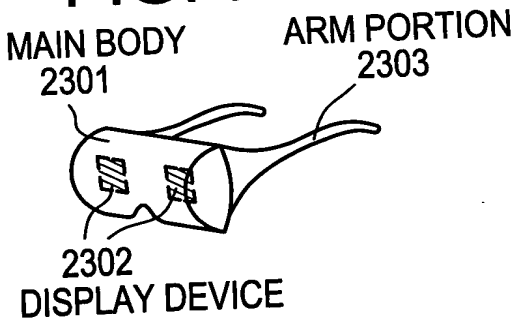


FIG. 7E

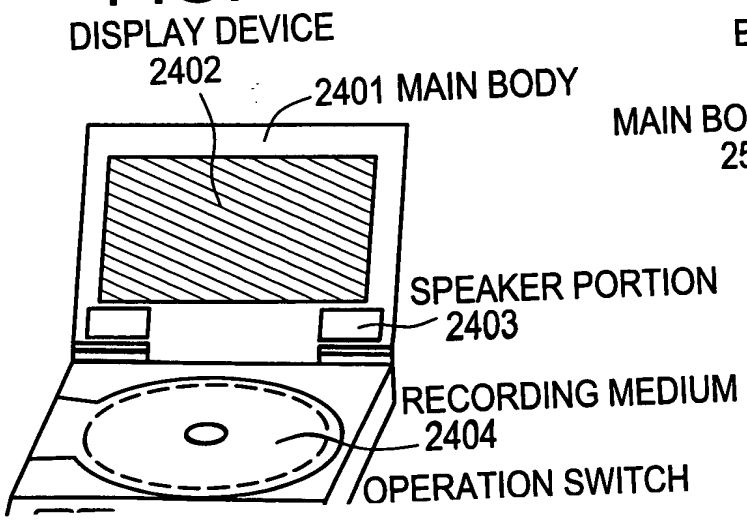


FIG. 7F

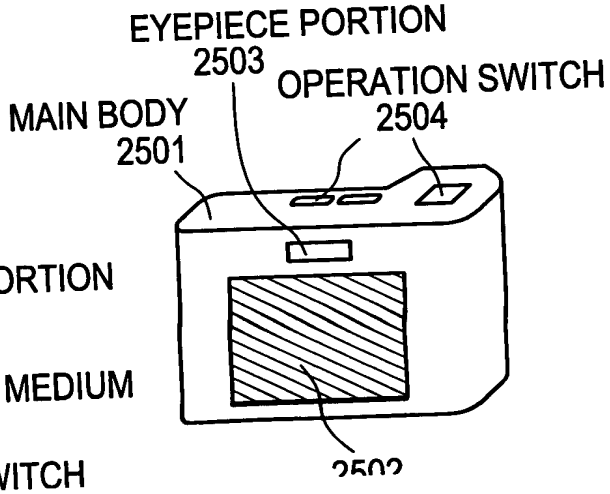


FIG. 8A

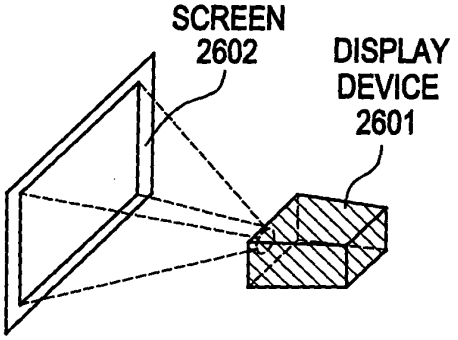


FIG. 8B

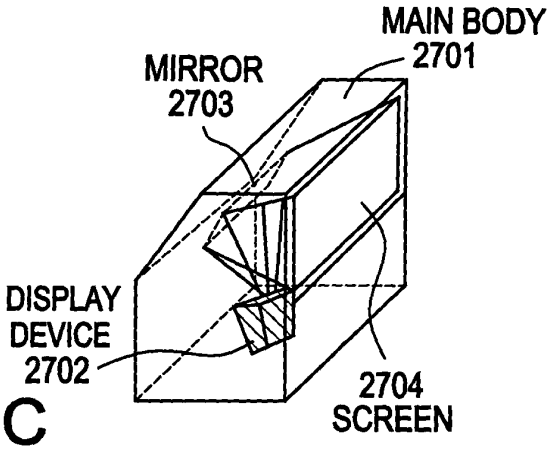


FIG. 8C

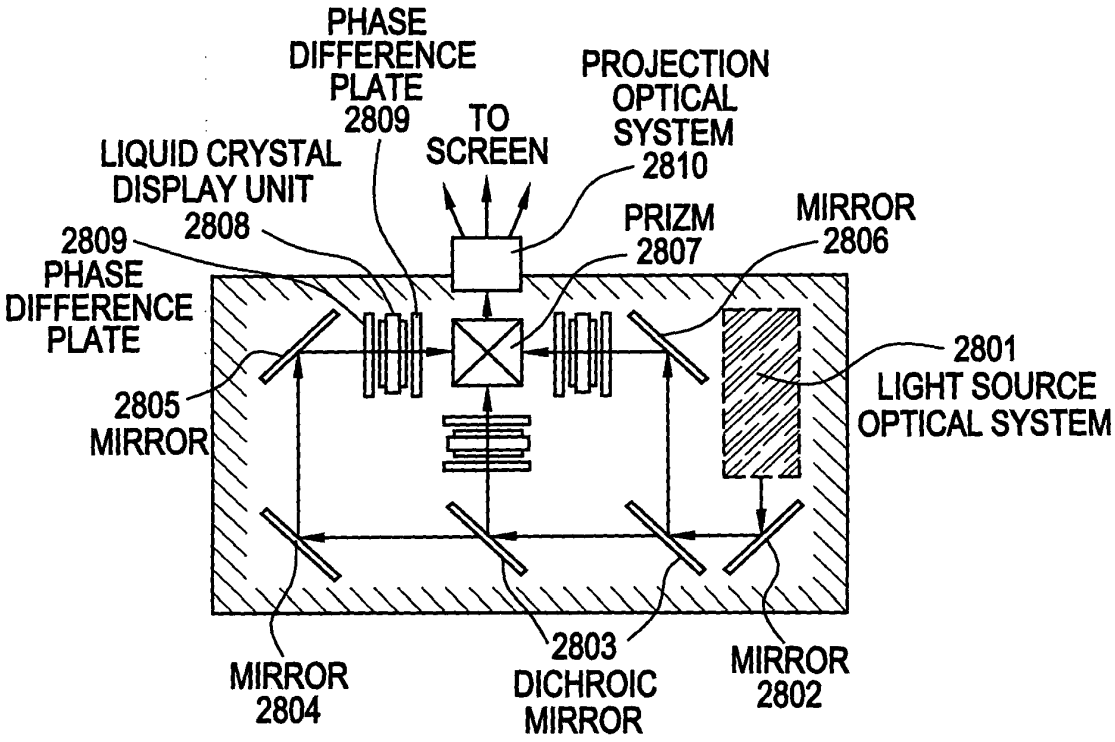


FIG. 8D

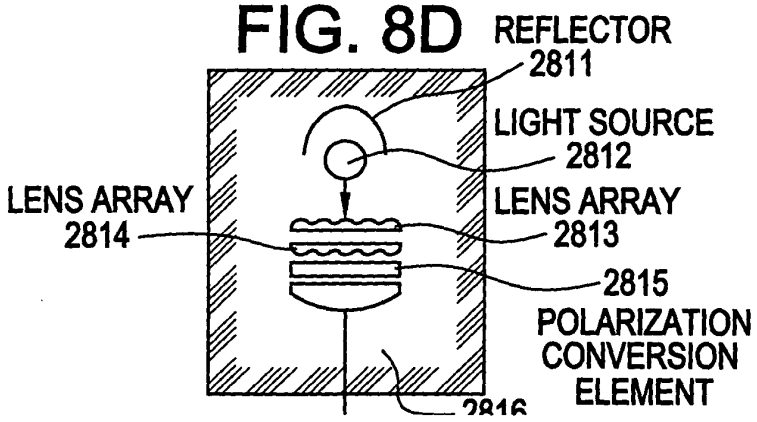


FIG. 9A

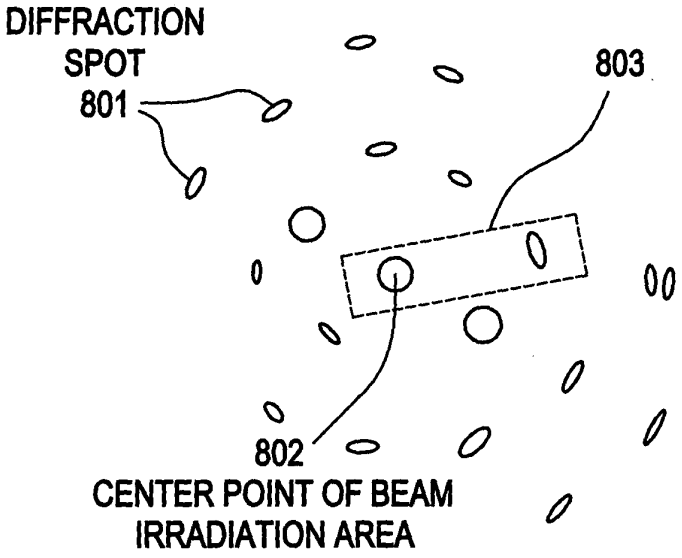


FIG. 9B

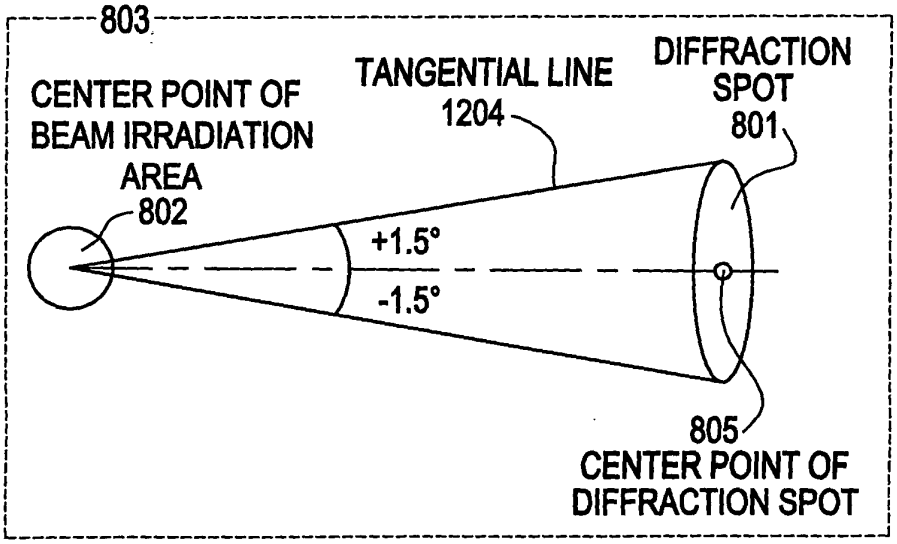


FIG. 10

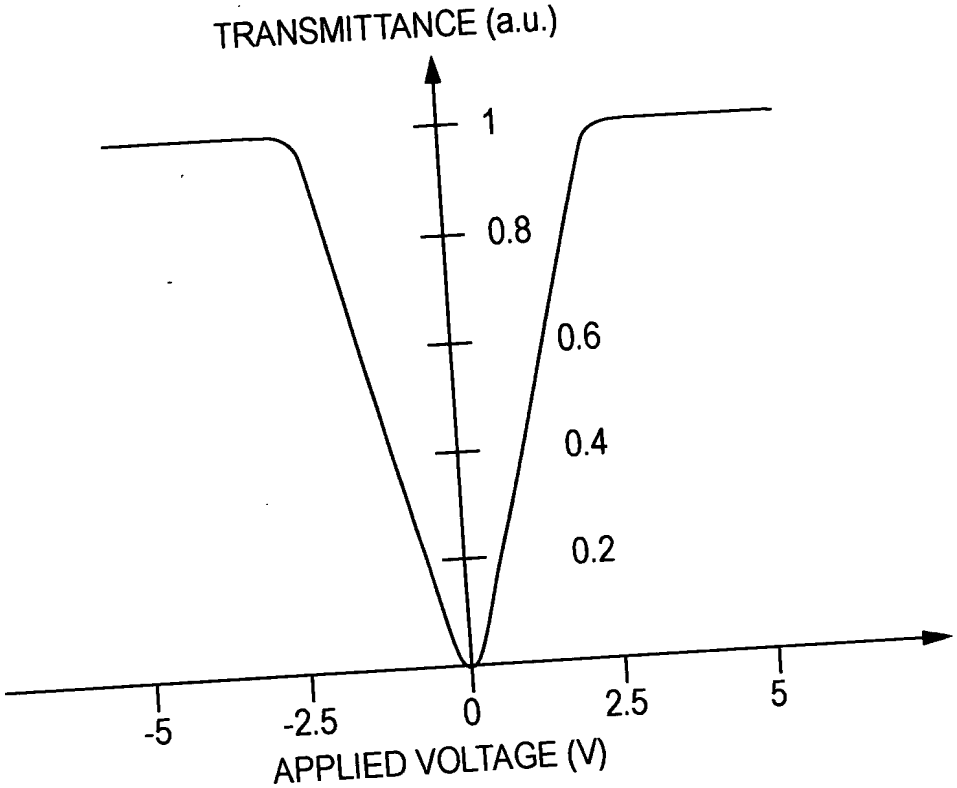
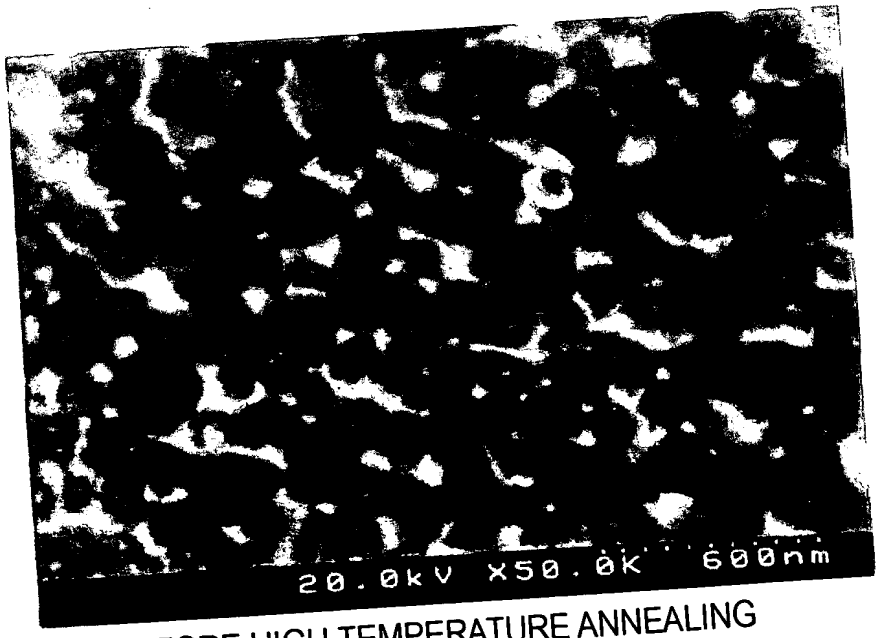
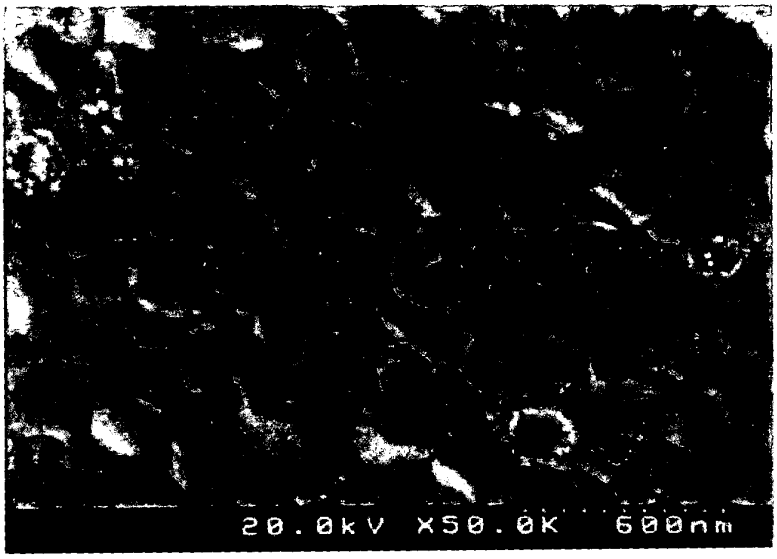


FIG. 11



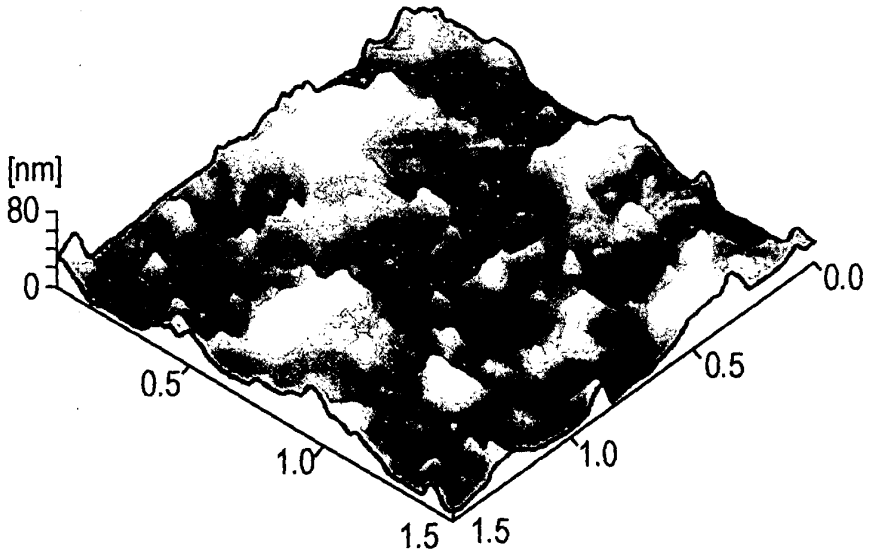
BEFORE HIGH TEMPERATURE ANNEALING

FIG. 12



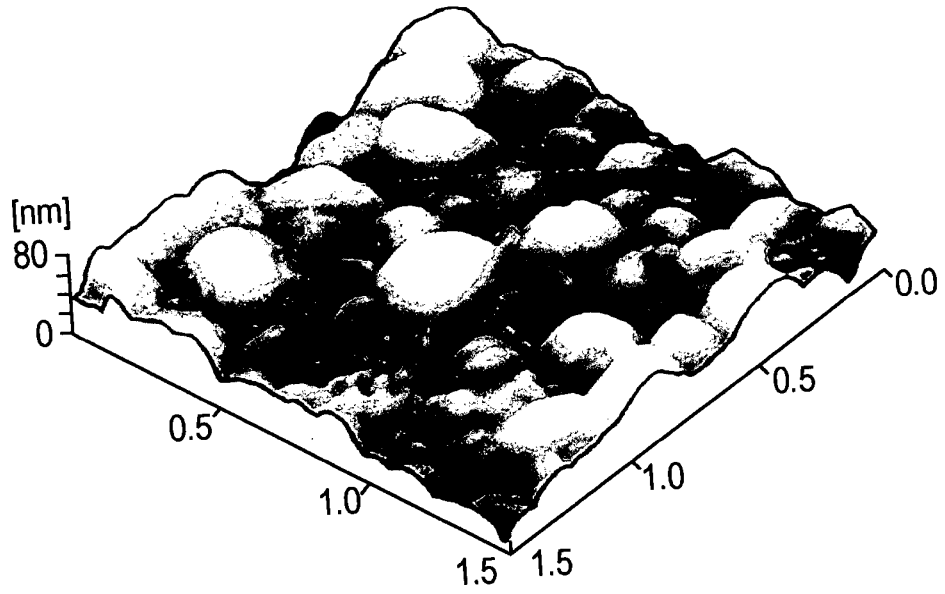
AFTER HIGH TEMPERATURE ANNEALING

FIG. 13



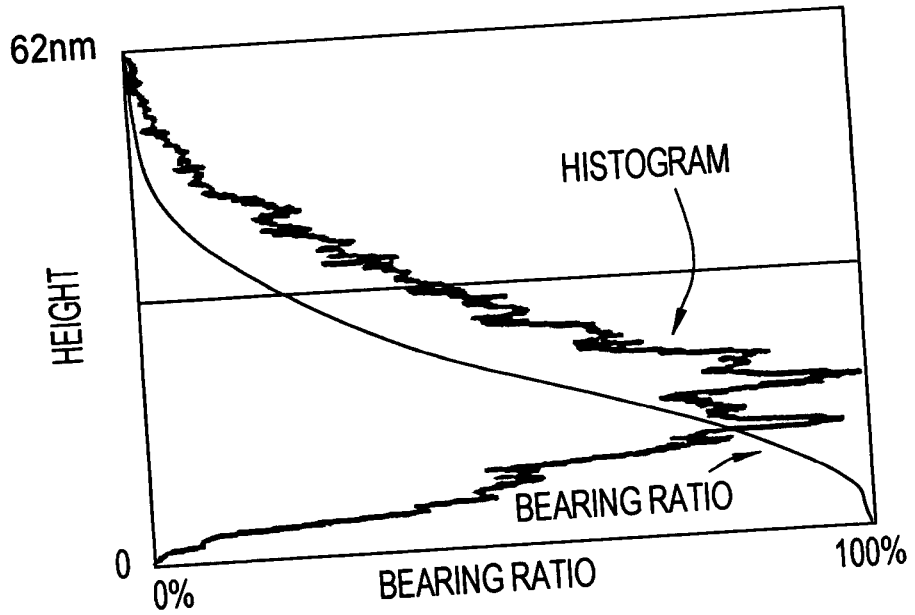
BEFORE HIGH TEMPERATURE ANNEALING

FIG. 14



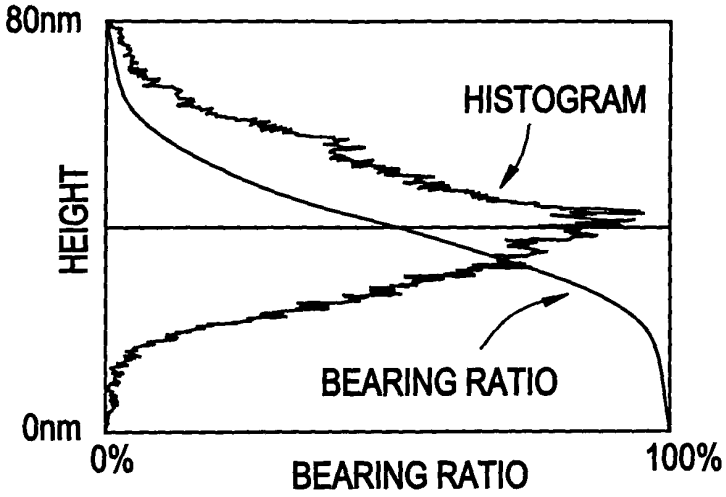
AFTER HIGH TEMPERATURE ANNEALING

FIG. 15



BEFORE HIGH TEMPERATURE ANNEALING

FIG. 16



AFTER HIGH TEMPERATURE ANNEALING

FIG. 17

OBSERVATION REGION	BEFORE HIGH TEMPERATURE ANNEALING	AFTER HIGH TEMPERATURE ANNEALING
1	13.623	40.925
2	20.027	51.126
3	20.629	59.364
4	21.798	48.539
5	16.666	55.341
6	15.097	46.510
7	13.120	57.655
8	14.035	51.120
9	12.599	54.416
10	20.699	36.945
MINIMUM VALUE (%)	12.60	36.95
MAXIMUM VALUE (%)	21.80	59.36
AVERAGE VALUE (%)	16.83	50.19
STANDARD DEVIATION σ	3.61	7.18